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(21)Application number : 63-325220 (71)Applicant : NEC CORP

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(54) METHOD FOR GROWING SEMICONDUCTOR CRYSTAL

(57)Abstract:

PURPOSE: To uniformly grow an SiC crystal film having a thickness controlled on the order of an atomic layer by CVD on the entire surface of a substrate having a large area by alternately introducing a mixture of gaseous hydrogen chloride with gaseous silicon chloride and gaseous hydrocarbon into a growth system.
CONSTITUTION: When an SiC crystal is grown by CVD with gaseous silicon chloride and gaseous hydrocarbon as starting materials, a mixture of gaseous hydrogen chloride with gaseous silicon chloride such as SiH₂Cl₂ and gaseous hydrocarbon such as C₂H₂ are alternately introduced into a growth system and an SiC crystal film is grown. Gaseous carbon chloride may be introduced in place of the gaseous hydrocarbon.

LEGAL STATUS

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